

---

# HR1107CR

InGaAs PIN Photodiode

# HITACHI

---

## Description

The HR1107CR is an InGaAs PIN photodiode for detecting light in the 1.0  $\mu\text{m}$  to 1.65  $\mu\text{m}$  band. Its fast pulse response makes it suitable as an optical signal detector in high-bit-rate fiberoptic communications equipment.

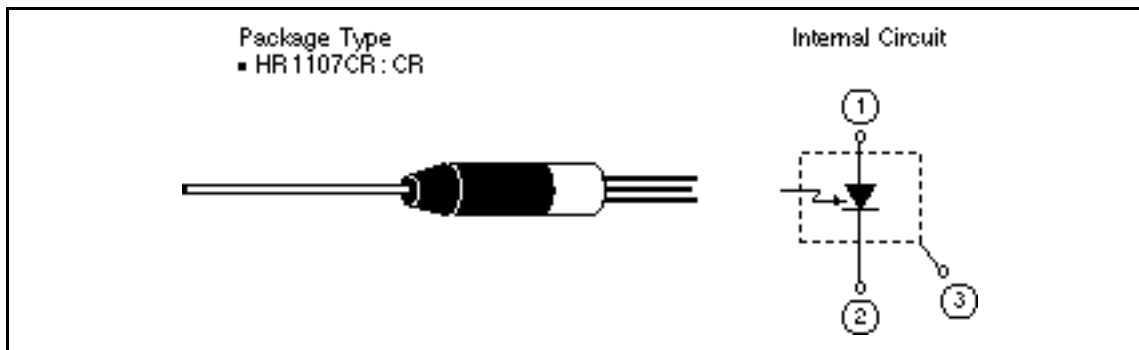
## Features

- Σ Fast pulse response:  $t_r, t_f = 0.3 \text{ ns Typ}$
- Σ High sensitivity:  $S = 0.8 \text{ mA/mW Typ (} \lambda_p = 1550 \text{ nm)}$
- Σ Low dark current:  $I_{\text{DARK}} = 1 \text{ nA Typ}$
- Σ Low capacitance:  $C_t = 0.9 \text{ pF Typ}$
- Σ Photodetectable area: 80  $\mu\text{m Dia}$

## Fiber Specifications

- Σ Numerical aperture: 0.2
- Σ Core diameter: 50  $\mu\text{m}$
- Σ Outer diameter: 125  $\mu\text{m}$
- Σ Jacket diameter: 900  $\mu\text{m}$
- Σ Refractive index profile: GI
- Σ Fiber length: More than 1000 mm

## HR1107CR



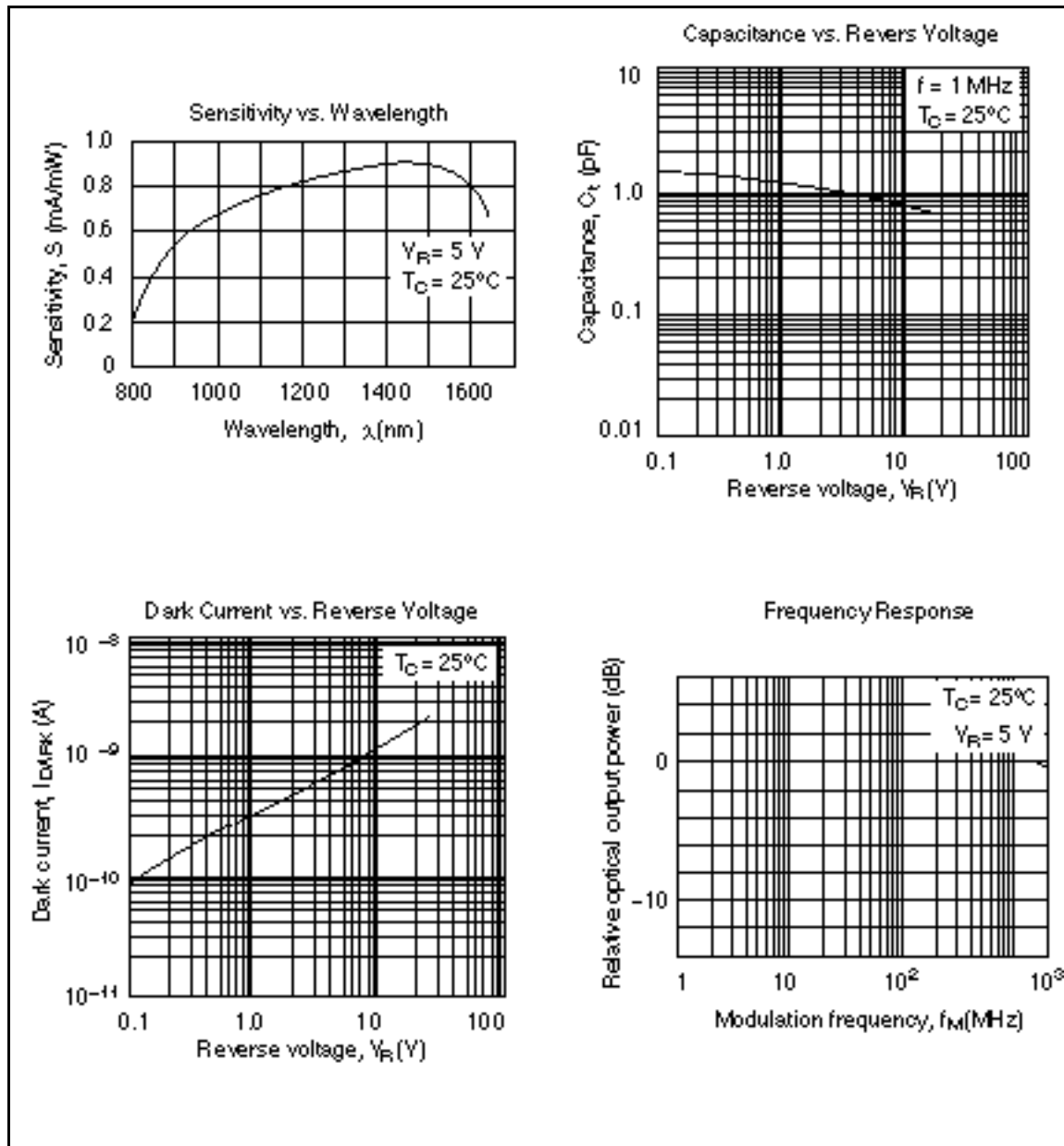
### Absolute Maximum Ratings ( $T_C = 25^\circ\text{C}$ )

| Item                  | Symbol    | Rated Value    | Unit             |
|-----------------------|-----------|----------------|------------------|
| Reverse voltage       | $V_R$     | 20             | V                |
| Forward current       | $I_F$     | 5.0            | mA               |
| Reverse current       | $I_R$     | 500            | $\mu\text{A}$    |
| Operating temperature | $T_{opr}$ | $-20$ to $+70$ | $^\circ\text{C}$ |
| Storage temperature   | $T_{stg}$ | $-40$ to $+85$ | $^\circ\text{C}$ |

### Optical and Electrical Characteristics ( $T_C = 25^\circ\text{C}$ )

| Item                                | Symbol            | Min  | Typ  | Max | Unit  | Test Conditions                                                          |
|-------------------------------------|-------------------|------|------|-----|-------|--------------------------------------------------------------------------|
| Dark current                        | $I_{\text{DARK}}$ | —    | 1    | 5   | nA    | $V_R = 5\text{ V}$                                                       |
| Capacitance                         | $C_t$             | —    | 0.9  | 1.3 |       | $V_R = 5\text{ V}$ , $f = 1\text{ MHz}$                                  |
| Sensitivity                         | $S_1$             | 0.70 | 0.78 | —   | mA/mW | $V_R = 5\text{ V}$ , $\lambda_p = 1300\text{ nm}$                        |
|                                     | $S_2$             | —    | 0.8  |     | mA/mW | $V_R = 5\text{ V}$ , $\lambda_p = 1550\text{ nm}$                        |
| Photosensitivity saturation voltage | $V_{R(S)}$        | —    | —    | 2   | V     |                                                                          |
| Rise time                           | $t_r$             | —    | 0.3  | —   | ns    | $V_R = 5\text{ V}$ , $\lambda_p = 1300\text{ nm}$<br>$R_L = 50\text{ W}$ |
| Fall time                           | $t_f$             | —    | 0.3  | —   | ns    | $V_R = 5\text{ V}$ , $\lambda_p = 1300\text{ nm}$<br>$R_L = 50\text{ W}$ |

Typical Characteristic Curves



**Typical Characteristic Curves (cont)**
